



DDTC114ELP

PRE-BIASED (R1 = R2) SMALL SIGNAL SURFACE MOUNT 100mA NPN TRANSISTOR

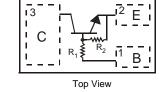
Features

- Epitaxial Planar Die Construction
- Ultra-Small Leadless Surface Mount Package
- Ideally Suited for Automated Assembly Processes
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

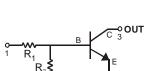
- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: Collector Dot (See Diagram and Marking Information)
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Code N5, Dot denotes Collector Side
- Ordering Information: See Page 4
- Weight: 0.0009 grams (approximate)

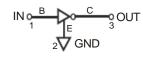




DFN1006-3

GND





Schematic and Pin Configuration

Equivalent Inverter Circuit

Component P/N	R1(NOM)	R2(NOM)
DDTC114ELP	10K	10K

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	-10 to +40	V
Output Current	Ι _Ο	50	mA
Collector Current	I _{c(max)}	100	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) $@T_A = 25^{\circ}C$	PD	250	mW
Power Derating above 25°C	P _{der}	2	mW/°C
Thermal Resistance, Junction to Ambient Air (Note 3) $@T_A = 25^{\circ}C$ (Equivalent to one heated junction of NPN)	$R_{ extsf{ heta}JA}$	500	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	С°

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

 Device mounted on FR-4 PCB, 1" x 0.85" x 0.062"; pad layout as shown on page 5 or Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

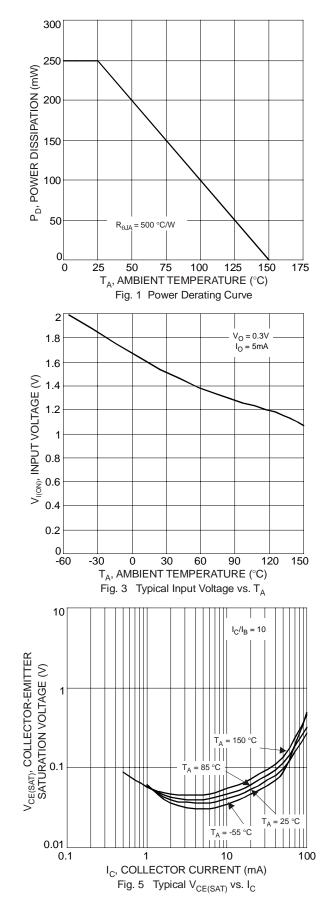


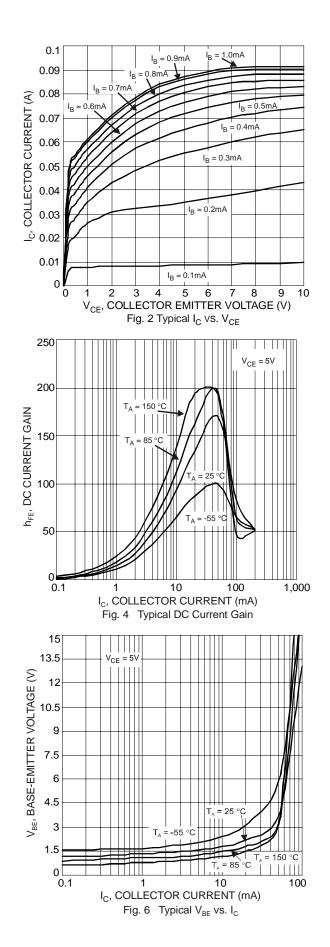
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Off Characteristics (Note 4)			-	-		
Collector-Base Breakdown Voltage	V _{(BR)CBO}	50			V	$I_{C} = 10 \mu A, I_{E} = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	50	_	_	V	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage*	V _{(BR)EBO}	5			V	$I_E = 50 \mu A, I_C = 0$
Collector Cutoff Current*	I _{CEX}		_	0.5	μA	$V_{CE} = 50V, V_{EB(OFF)} = 3.0V$
Base Cutoff Current (I _{BEX})	I _{BL}		_	0.5	μA	$V_{CE} = 50V, V_{EB(OFF)} = 3.0V$
Collector-Base Cut Off Current	Ісво		_	0.5	μΑ	$V_{CB} = 50V, I_E = 0$
Collector-Emitter Cut Off Current, I _{O(OFF)}	I _{CEO}		_	1	μA	$V_{CB} = 50V, I_B = 0$
Emitter-Base Cut Off Current	I _{EBO}		—	0.4	mA	$V_{EB} = 4V, I_{C} = 0$
Input Off Voltage	V _{I(OFF)}		1.16	0.5	V	$V_{CC} = 5V, I_{O} = 100uA$
On Characteristics (Note 4)			•	•		
DC Current Gain		10	_	_		$V_{CE} = 5V, I_C = 1mA$
		15	_	_	_	$V_{CE} = 5V, I_C = 2mA$
	h _{FE}	60	_	_	_	$V_{CE} = 5V$, $I_C = 10mA$
		100	_	_	_	$V_{CE} = 5V, I_C = 50mA$
		90	_	_	_	$V_{CE} = 5V$, $I_C = 70$ mA
	V _{CE} (SAT)		_	0.15	V	$I_{\rm C}$ = 10mA, $I_{\rm B}$ = 1mA
			_	0.2	V	$I_{\rm C}$ = 50mA, $I_{\rm B}$ = 5mA
Collector-Emitter Saturation Voltage			_	0.25	V	$I_{\rm C} = 50 {\rm mA}, I_{\rm B} = 2.5 {\rm mA}$
			_	0.25	V	I _C = 50mA, I _B = 10mA
			_	0.3	V	I _C = 70mA, I _B = 10mA
	V _{BE(ON)}		_	0.85	V	$V_{CE} = 5V, I_C = 2mA$
Base-Emitter Turn-On Voltage*			_	0.95	V	$V_{CE} = 5V$, $I_C = 10mA$
	VBE(SAT)		_	0.98	V	$I_{C} = 10mA$, $I_{B} = 1mA$, $V_{CE} = 5V$
Base-Emitter Saturation Voltage*			_	1.2	V	$I_{C} = 50 \text{mA}, I_{B} = 5 \text{mA}, V_{CE} = 5 \text{V}$
Input-On Voltage	V _{I(ON)}	2.5	1.6		V	$V_{O} = 0.3V, I_{O} = 50mA$
Input Current	h	_	_	0.88	mA	V1 = 5V
Output On Voltage (Same as V _{CE(SAT)})	V _{O(ON)}			0.3	V	I _I = 2.5mA, I _O = 50mA
Input Resistance	R1	7	10	13	KΩ	_
Resistance Ratio	(R2/R1)	0.8	1	1.2	_	_
Small Signal Characteristics	i	I	•		1	
Current Gain-Bandwidth Product	f⊤		250	_	MHz	V _{CE} = 10V, I _E = 5mA, f = 1MHz

* Guaranteed by design.

Note: 4. Short duration pulse test used to minimize self-heating effect. Pulse Test: Pulse width tp<300 us, Duty Cycle, d<=2%.

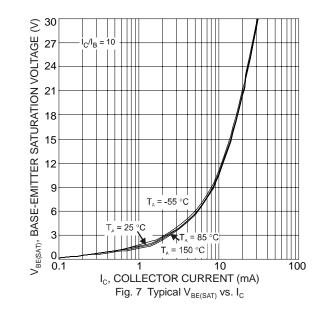






NEW PRODUCT





Ordering Information (Note 6)

Device	Packaging	Shipping
DDTC114ELP-7	DFN1006-3	3000/Tape & Reel

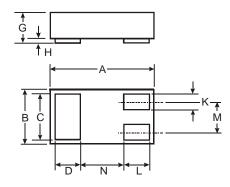
Notes: 6. For packaging details, please see page 5 or go to our website at http://www.diodes.com/ap2007.pdf.

Marking Information

N5

N5 = Product Type Marking Code Dot Denotes Collector, Pin 3

Package Outline Dimensions

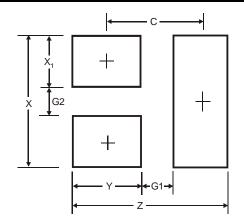


DFN1006-3				
Dim	Min	Max	Тур	
Α	0.95	1.075	1.00	
В	0.55	0.675	0.60	
С	0.45	0.55	0.50	
D	0.20	0.30	0.25	
G	0.47	0.53	0.50	
н	0	0.05	0.03	
κ	0.10	0.20	0.15	
L	0.20	0.30	0.25	
М	_	_	0.35	
Ν	_	_	0.40	
All Dimensions in mm				

NEW PRODUCT



Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
Х	0.7
X1	0.25
Y	0.4
C	0.7

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